

CM02D60-SOP8

Data Sheet

Version: 1.0

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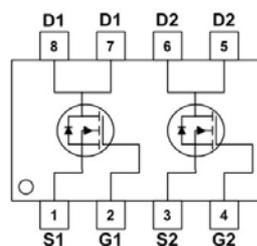
1. 650V 7.5Ω Dual N-Channel Power MOSFET Features

- Originative New Design
- Superior Avalanche Rugged Technology
- Robust Gate Oxide Technology
- Very Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Unrivalled Gate Charge : 4nC (Typ.)
- Extended Safe Operating Area

2. Applications

- Switching Mode Power Supply
- HID Lamp
- BLDC Motor

3. Pin Description



4. Absolute Ratings ($T_A = 25^\circ\text{C}$ in a SOP8 package unless otherwise noted)

| Parameter | Symbol | Value | Units |
|------------------------------|---------------|------------|------------------|
| Drain-Source Voltage | V_{DS} | +600 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Junction Temperature Maximum | T_{JMAX} | 150 | $^\circ\text{C}$ |
| Storage Temperature | $T_{Storage}$ | -25 to 150 | $^\circ\text{C}$ |

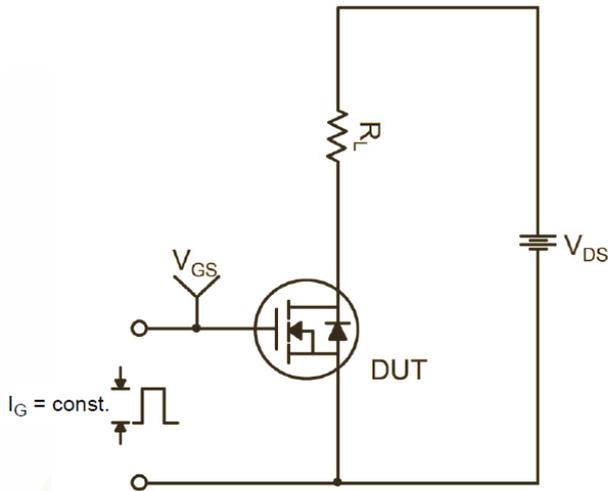
5. Thermal Characteristics

| Parameter | Symbol | Value | Units |
|-------------------------------------|-----------------|-------|---------------------------|
| Thermal Resistance Junction-Ambient | $R_{\theta JA}$ | 65 | $^\circ\text{C}/\text{W}$ |

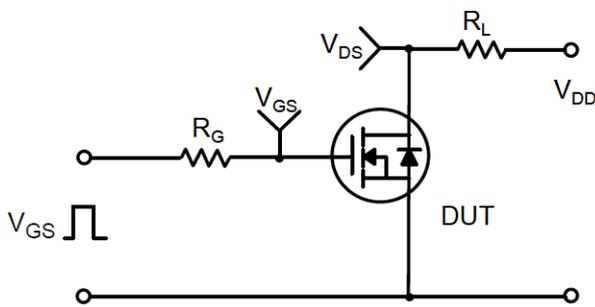
6. Electrical Characteristics

| Static ($T_J=25^\circ\text{C}$ unless otherwise specified) | | | | | | |
|---|--------------|---|------|------|-----------|----------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$ | 600 | --- | --- | V |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$ | --- | --- | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 500\text{V}, V_{GS} = 0\text{V}$ | --- | --- | 10 | uA |
| | | $V_{DS} = 400\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$ | --- | --- | 100 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{V}, I_D = 1\text{A}$ | --- | --- | 7.5 | Ω |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ | 1.5 | --- | 4 | V |
| Reverse Diode Characteristics | | | | | | |
| Continuous Source Current | I_S | $V_{GS} = 0\text{V}, V_{DS} \text{Open}, f=1\text{MHz}$ | --- | --- | 5.5 | A |
| Diode Forward Voltage | V_{SD} | $I_S = 0.8\text{A}, V_{GS} = 0\text{V}$ | --- | --- | 1.2 | V |
| Reverse Recovery Time | t_{rr} | $V_{GS} = 0\text{V}, I_S = 1\text{A}, dI_F/dt=50\text{A}/\mu\text{s}$ | --- | 50 | --- | ns |
| Reverse Recovery Charge | Q_{rr} | | --- | 18 | --- | nC |

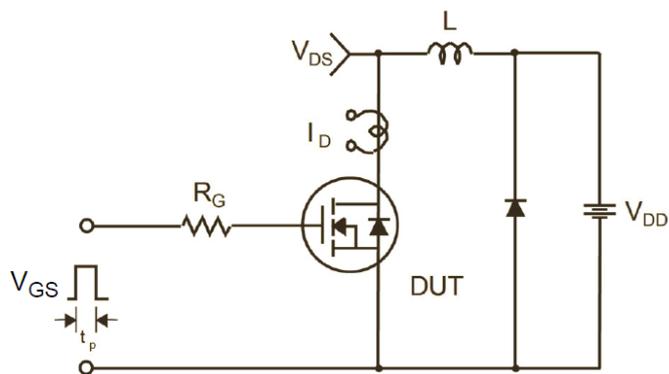
7. Test Circuit and Waveform



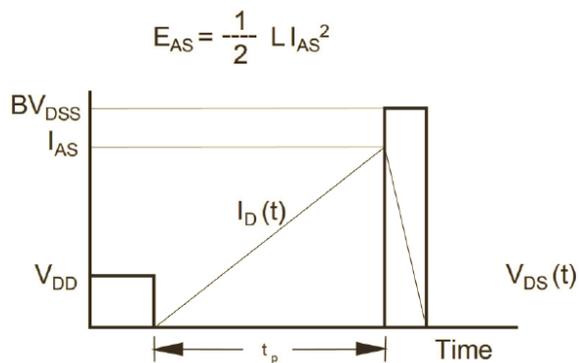
Gate Charge Test Circuit & Waveform

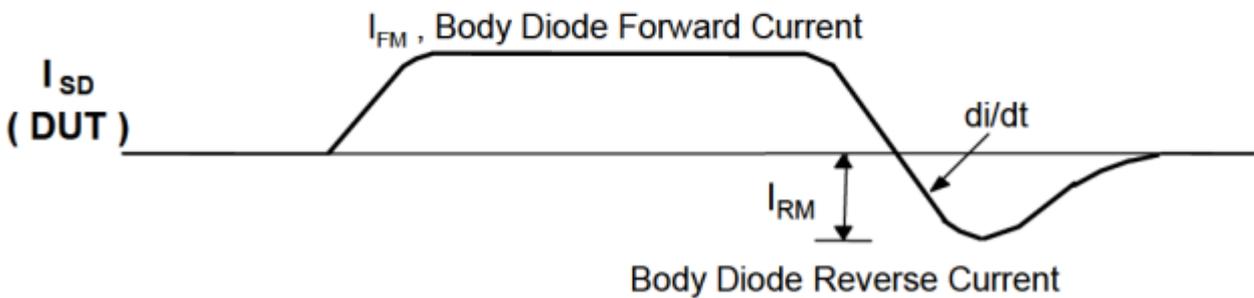
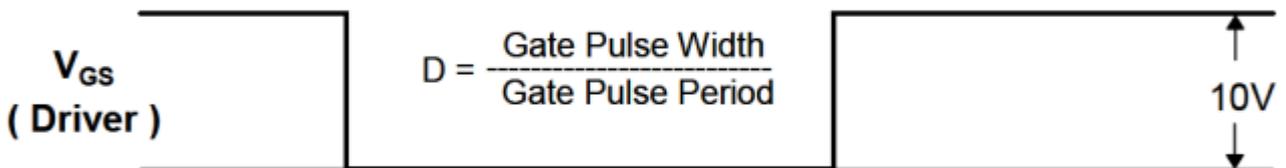
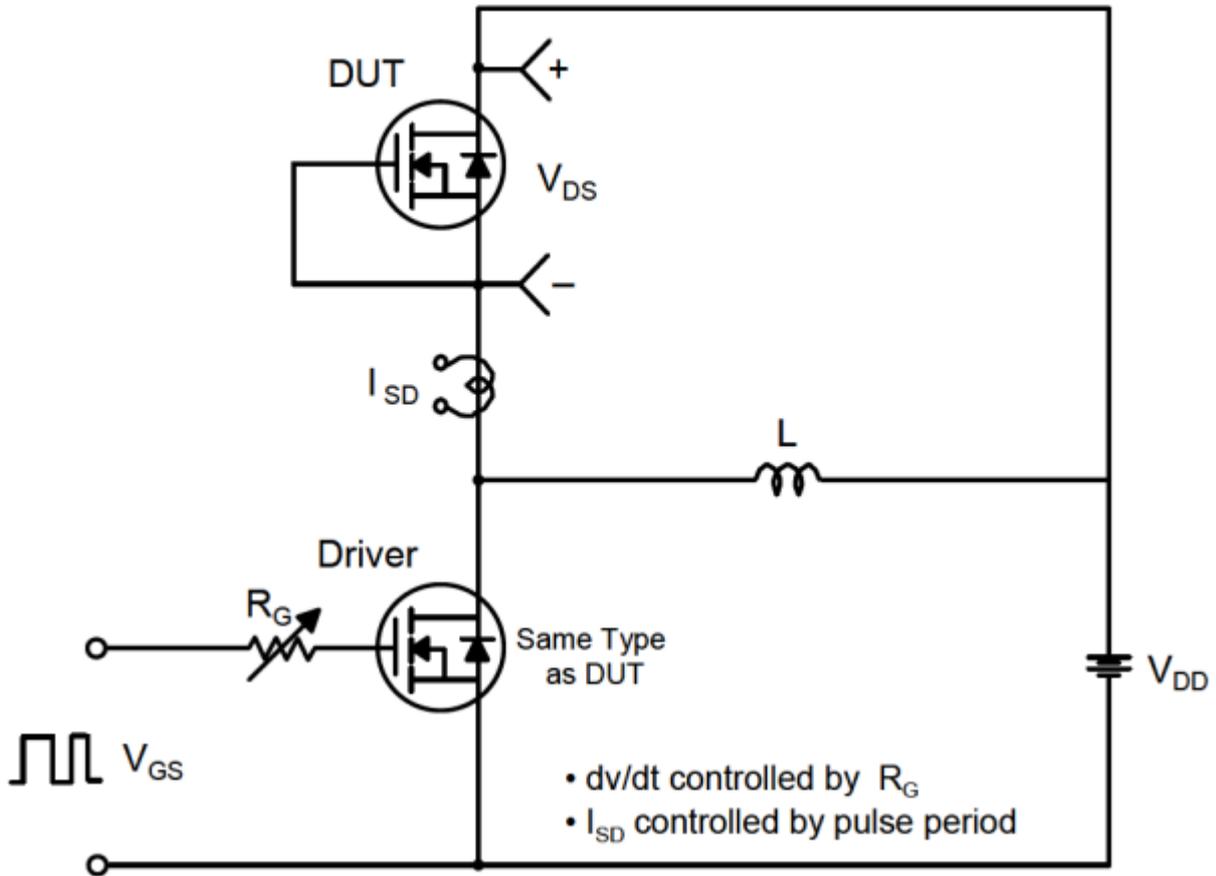


Resistive Switching Test Circuit & Waveforms



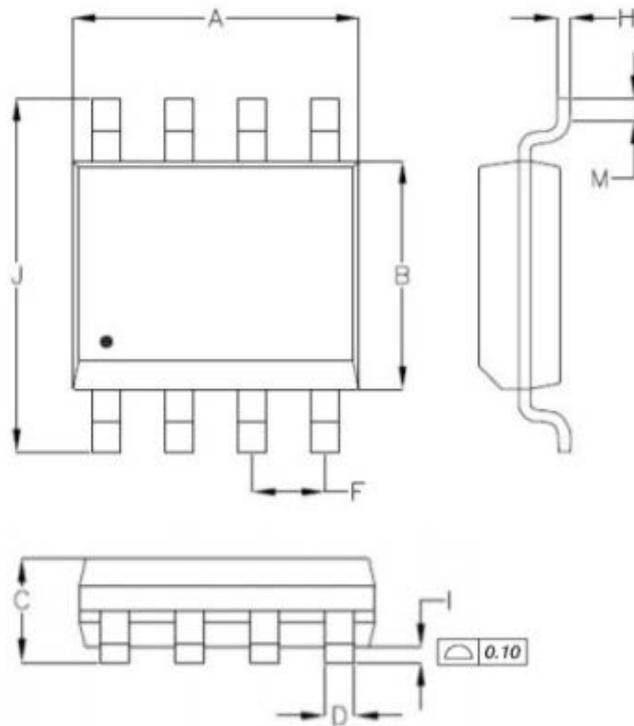
Unclamped Inductive Switching Test Circuit & Waveform





Peak Diode Recovery dv/dt Test Circuit & Waveforms

8. SOP8 Package Information



| SYMBOLS | MILLIMETERS | | INCHES | |
|---------|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.700 | 5.150 | 0.185 | 0.203 |
| B | 3.700 | 4.100 | 0.146 | 0.161 |
| C | 1.23 | 1.753 | 0.048 | 0.069 |
| D | 0.310 | 0.510 | 0.012 | 0.020 |
| F | 1.070 | 1.470 | 0.042 | 0.058 |
| H | 0.160 | 0.254 | 0.006 | 0.010 |
| I | 0.050 | 0.254 | 0.002 | 0.010 |
| J | 5.750 | 6.250 | 0.226 | 0.246 |
| M | 0.400 | 1.270 | 0.016 | 0.050 |

9. Marking Distinguish

